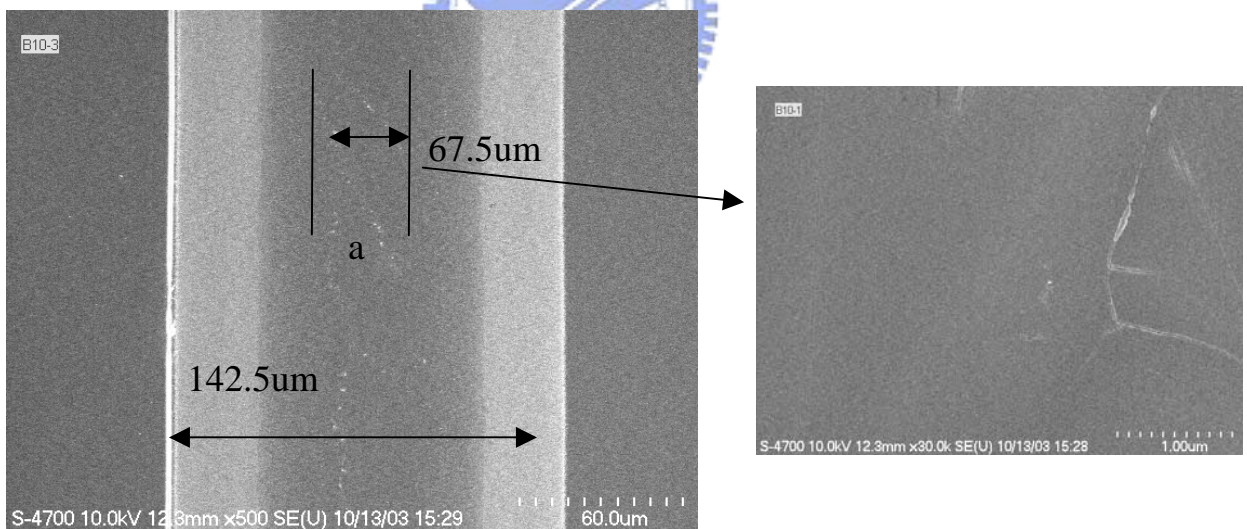
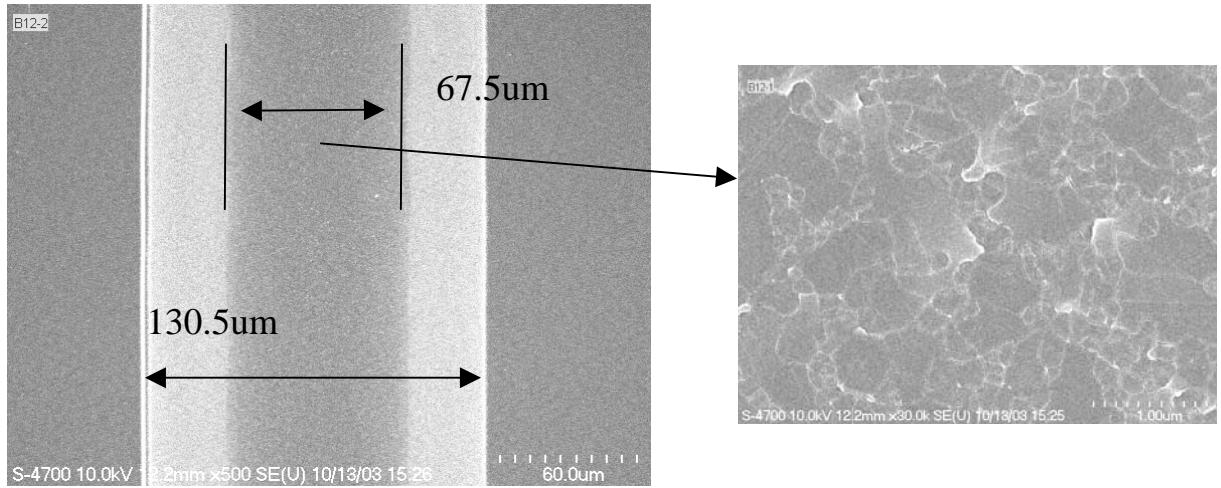


**Fig. 4-23** SEM micrographs of CW laser crystallized poly-Silicon films after Secco etching for 60sec treatment. The constant laser power is 4W with backside irradiation. The scan speed is 7cm/sec



**Fig. 4-24** SEM micrographs of CW laser crystallized poly-Silicon films after Secco etching for 60sec treatment. The constant laser power is 4W with backside irradiation. The scan speed is 10cm/sec, the grain size of area "a" is larger than 3um



**Fig. 4-25** SEM micrographs of CW laser crystallized poly-Silicon films after Secco etching for 60sec treatment. The constant laser power is 4W with backside irradiation. The scan speed is 12cm/sec, the grain size of center area is smaller than 1um

